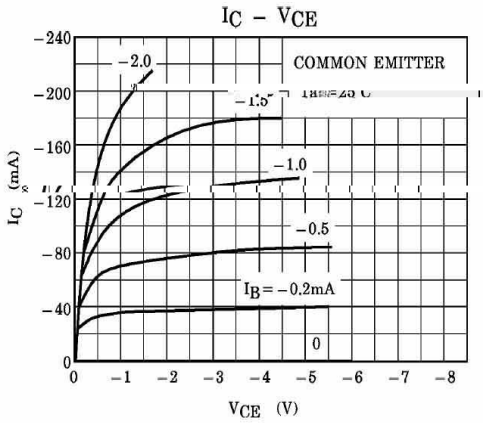
SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

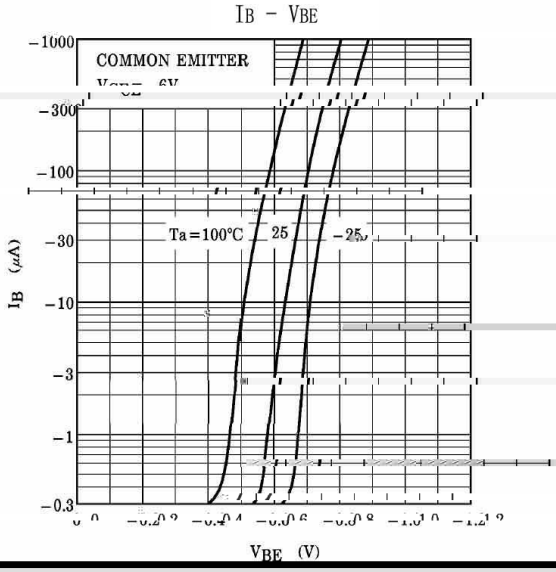
, , h_{FE} , , 2SC1815M

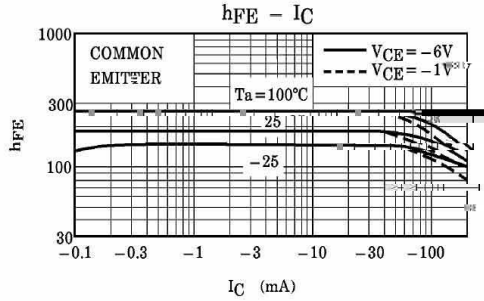
High voltage and high current, excellent h_{FE}1

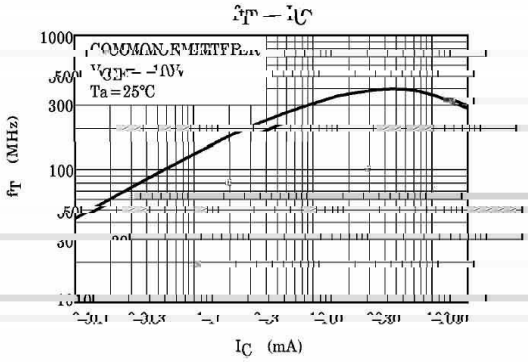
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-150	mA
Base Current	I_B	-50	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55˙ 150	

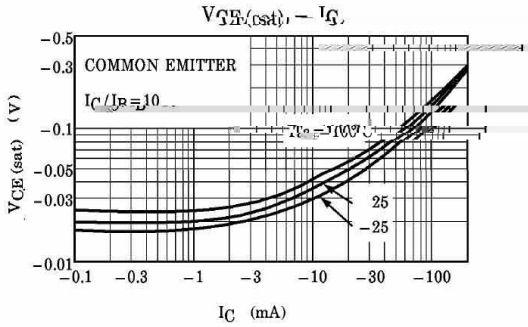
Parameter Symbol

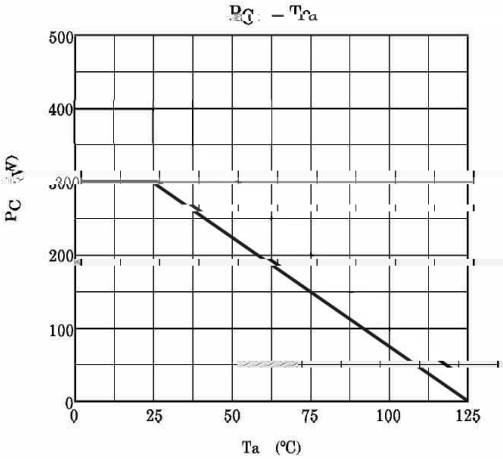

I_C – V_{CE}
COMMON EMITTER
−2.0
−1.5
−1.0
−0.5
I_B = −0.2mA
0
I_C (mA)
V_{CE} (V)

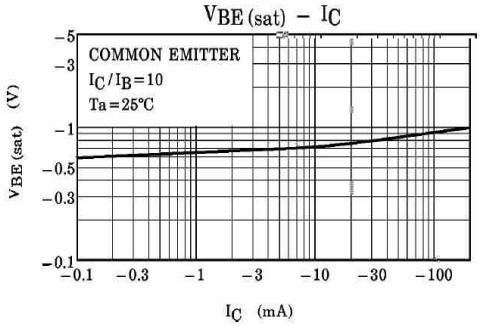

I_B – V_{BE}
COMMON EMITTER
Ta=100°C
25
−25
I_B (μA)
V_{BE} (V)

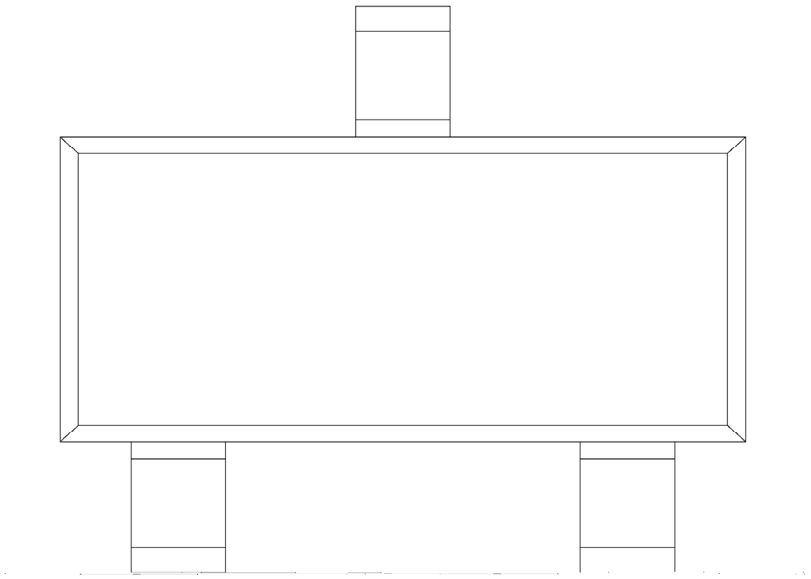

h_{FE} – I_C
COMMON EMITTER
V_{CE} = −6V
V_{CE} = −1V
Ta=100°C
25
−25
h_{FE}
I_C (mA)


f_T – I_C
COMMON EMITTER
V_{CE} = −10V
Ta=25°C
f_T (MHz)
I_C (mA)


$V_{CE(sat)}$ – I_C
COMMON EMITTER
I_C/I_B = 10
Ta=100°C
25
−25
V_{CE} (sat) (V)
I_C (mA)


P_C – T_a
P_C (W)
Ta (°C)


$V_{BE(sat)}$ – I_C
COMMON EMITTER
I_C/I_B = 10
Ta=25°C
V_{BE} (sat) (V)
I_C (mA)



H

BA

O: h_{FE}

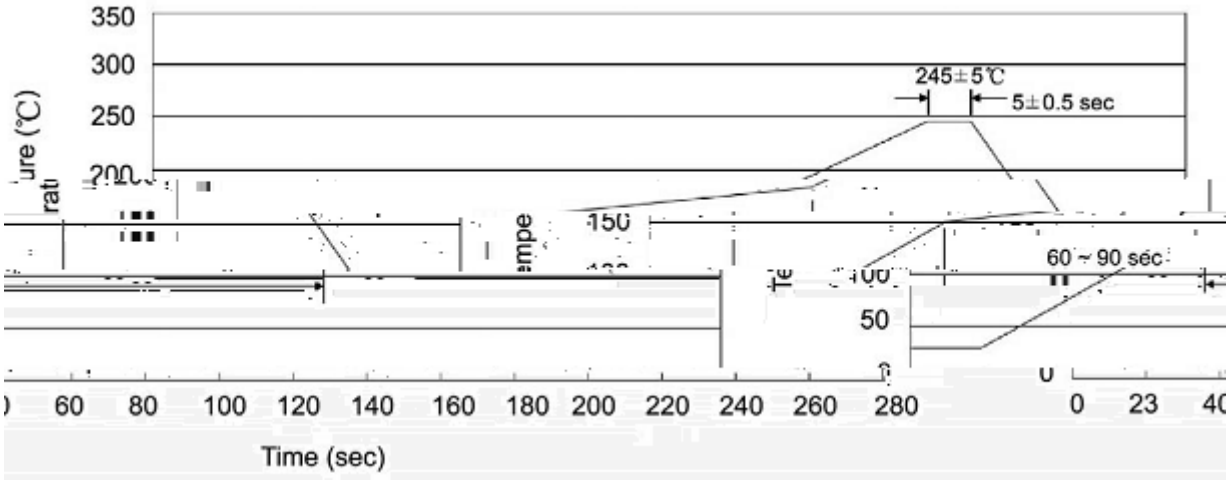
Note:

H: Company Code.

BA: Product Type Code

O: h_{FE}

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1 25 150 60 90sec;

2 245±5 5±0.5sec;

3 2 10 /sec.

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

260±5 10±1 sec.

Temp.:260±5 Time:10±1 sec

/ REEL

Package Type	Units					Dimension		(unit mm^3)
						ρ		